

8A, 400V - 600V Hyperfast Diodes

The RHRP840 and RHRP860 are hyperfast diodes with soft recovery characteristics ($t_{rr} < 30ns$). They have half the recovery time of ultrafast diodes and are silicon nitride passivated ion-implanted epitaxial planar construction.

These devices are intended for use as freewheeling/clamping diodes and rectifiers in a variety of switching power supplies and other power switching applications. Their low stored charge and hyperfast soft recovery minimize ringing and electrical noise in many power switching circuits reducing power loss in the switching transistors.

Formerly developmental type TA49059.

Ordering Information

PART NUMBER	PACKAGE	BRAND
RHRP840	TO-220AC	RHRP840
RHRP860	TO-220AC	RHRP860

NOTE: When ordering, use the entire part number.

Symbol



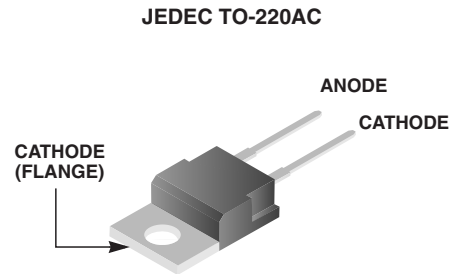
Features

- Hyperfast with Soft Recovery <30ns
- Operating Temperature 175°C
- Reverse Voltage Up To 600V
- Avalanche Energy Rated
- Planar Construction

Applications

- Switching Power Supplies
- Power Switching Circuits
- General Purpose

Packaging



Absolute Maximum Ratings $T_C = 25^\circ C$, Unless Otherwise Specified

	RHRP840	RHRP860	UNITS
Peak Repetitive Reverse Voltage V_{RRM}	400	600	V
Working Peak Reverse Voltage V_{RWM}	400	600	V
DC Blocking Voltage V_R	400	600	V
Average Rectified Forward Current $I_{F(AV)}$ ($T_C = 150^\circ C$)	8	8	A
Repetitive Peak Surge Current I_{FRM} (Square Wave, 20kHz)	16	16	A
Nonrepetitive Peak Surge Current I_{FSM} (Halfwave, 1 Phase, 60Hz)	100	100	A
Maximum Power Dissipation P_D	75	75	W
Avalanche Energy (See Figures 10 and 11) E_{AVL}	20	20	mJ
Operating and Storage Temperature T_{STG}, T_J	-65 to 175	-65 to 175	°C

RHRP840, RHRP860

Electrical Specifications $T_C = 25^\circ\text{C}$, Unless Otherwise Specified

SYMBOL	TEST CONDITION	RHRP840			RHRP860			UNITS
		MIN	TYP	MAX	MIN	TYP	MAX	
V_F	$I_F = 8\text{A}$	-	-	2.1	-	-	2.1	V
	$I_F = 8\text{A}, T_C = 150^\circ\text{C}$	-	-	1.7	-	-	1.7	V
I_R	$V_R = 400\text{V}$	-	-	100	-	-	-	μA
	$V_R = 600\text{V}$	-	-	-	-	-	100	μA
	$V_R = 400\text{V}, T_C = 150^\circ\text{C}$	-	-	500	-	-	-	μA
	$V_R = 600\text{V}, T_C = 150^\circ\text{C}$	-	-	-	-	-	500	μA
t_{rr}	$I_F = 1\text{A}, dI_F/dt = 200\text{A}/\mu\text{s}$	-	-	30	-	-	30	ns
	$I_F = 8\text{A}, dI_F/dt = 200\text{A}/\mu\text{s}$	-	-	35	-	-	35	ns
t_a	$I_F = 8\text{A}, dI_F/dt = 200\text{A}/\mu\text{s}$	-	18	-	-	18	-	ns
t_b	$I_F = 8\text{A}, dI_F/dt = 200\text{A}/\mu\text{s}$	-	10	-	-	10	-	ns
Q_{RR}	$I_F = 8\text{A}, dI_F/dt = 200\text{A}/\mu\text{s}$	-	56	-	-	56	-	nC
C_J	$V_R = 10\text{V}, I_F = 0\text{A}$	-	25	-	-	25	-	pF
$R_{\theta JC}$		-	-	2	-	-	2	$^\circ\text{C}/\text{W}$

DEFINITIONS

V_F = Instantaneous forward voltage ($p_w = 300\mu\text{s}$, $D = 2\%$).

I_R = Instantaneous reverse current.

t_{rr} = Reverse recovery time (See Figure 9), summation of $t_a + t_b$.

t_a = Time to reach peak reverse current (See Figure 9).

t_b = Time from peak I_{RM} to projected zero crossing of I_{RM} based on a straight line from peak I_{RM} through 25% of I_{RM} (See Figure 9).

Q_{RR} = Reverse recovery charge.

C_J = Junction capacitance.

$R_{\theta JC}$ = Thermal resistance junction to case.

p_w = Pulse width.

D = Duty cycle.

Typical Performance Curves

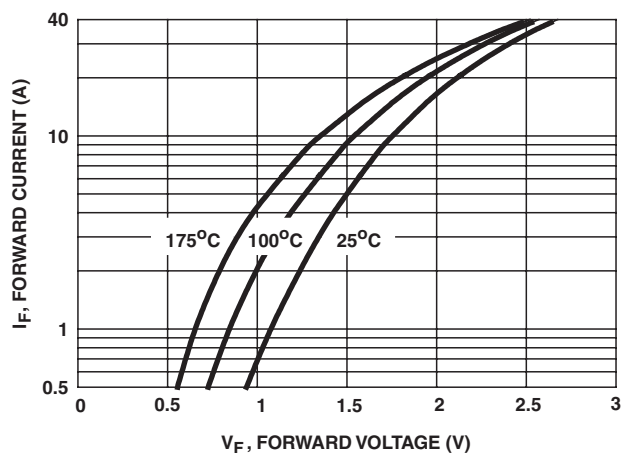


FIGURE 1. FORWARD CURRENT vs FORWARD VOLTAGE

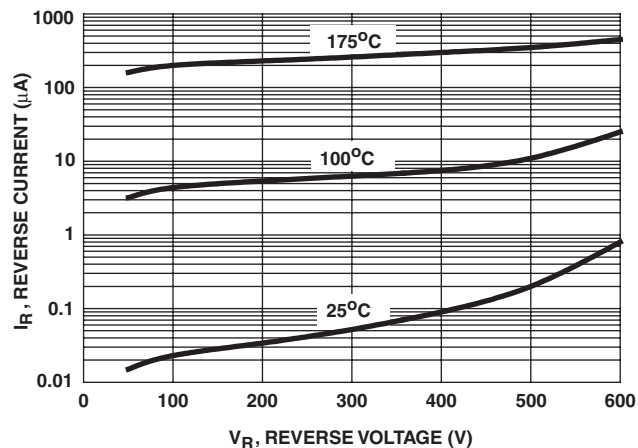


FIGURE 2. REVERSE CURRENT vs REVERSE VOLTAGE

Typical Performance Curves (Continued)

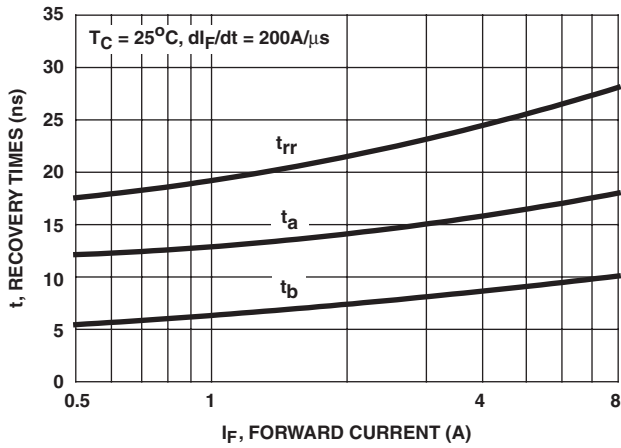


FIGURE 3. t_{rr} , t_a AND t_b CURVES vs FORWARD CURRENT

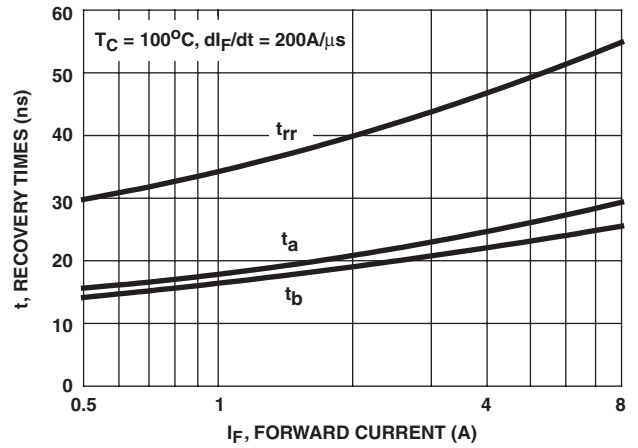


FIGURE 4. t_{rr} , t_a AND t_b CURVES vs FORWARD CURRENT

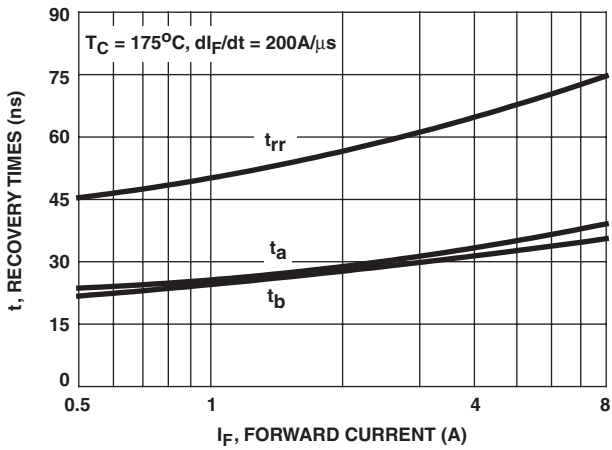


FIGURE 5. t_{rr} , t_a AND t_b CURVES vs FORWARD CURRENT

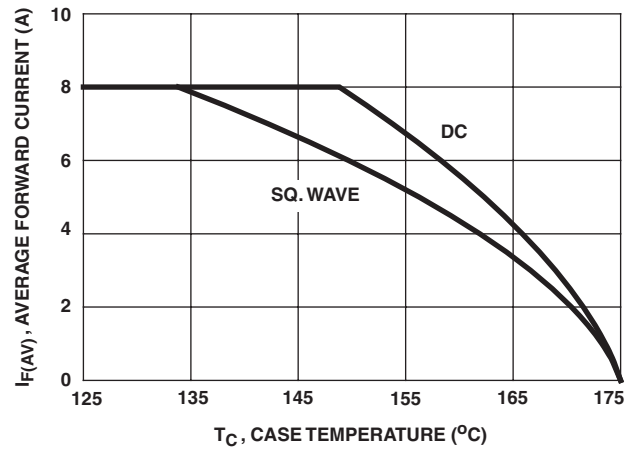


FIGURE 6. CURRENT DERATING CURVE

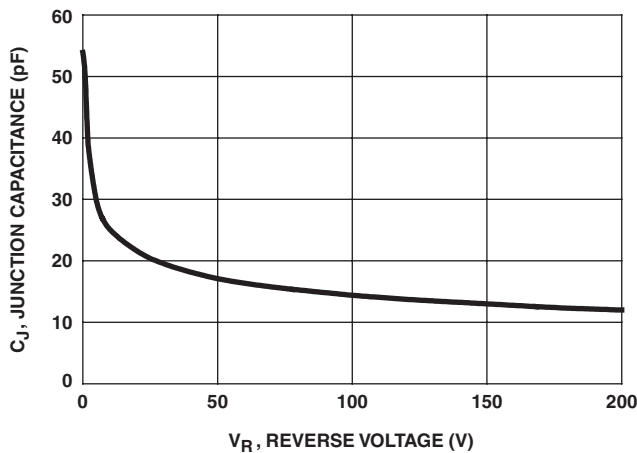


FIGURE 7. JUNCTION CAPACITANCE vs REVERSE VOLTAGE

Test Circuits and Waveforms

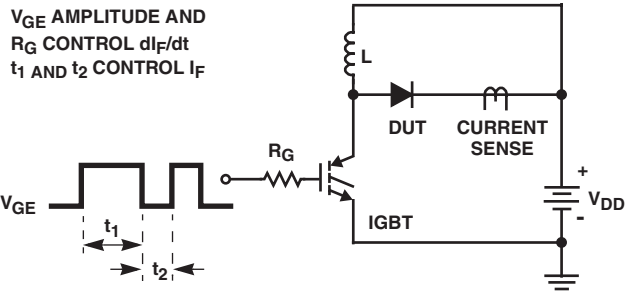


FIGURE 8. t_{rr} TEST CIRCUIT

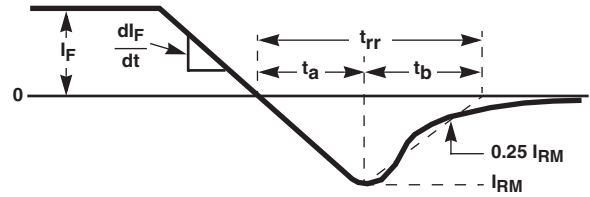


FIGURE 9. t_{rr} WAVEFORMS AND DEFINITIONS

$I_{MAX} = 1A$
 $L = 40mH$
 $R < 0.1\Omega$
 $E_{AVL} = 1/2LI^2 [V_{R(AVL)}/(V_{R(AVL)} - V_{DD})]$
 $Q_1 = IGBT (BV_{CES} > DUT V_{R(AVL)})$

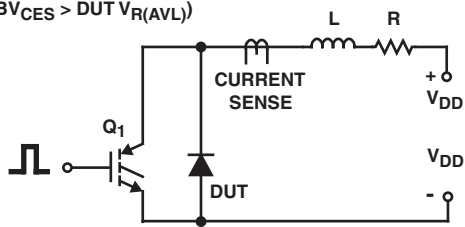


FIGURE 10. AVALANCHE ENERGY TEST CIRCUIT

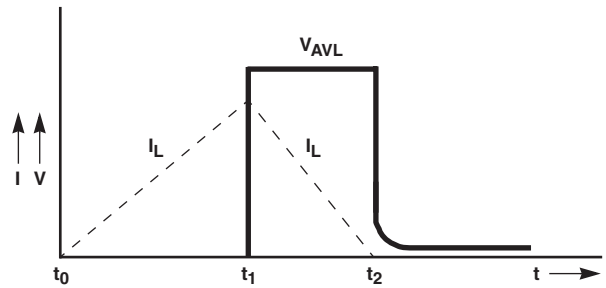


FIGURE 11. AVALANCHE CURRENT AND VOLTAGE WAVEFORMS

ACE _x TM	FAST ^â	OPTOLOGIC TM	SMART START TM	VCX TM
Bottomless TM	FAST _r TM	OPTOPLANAR TM	STAR*POWER TM	
CoolFET TM	FRFET TM	PACMAN TM	Stealth TM	
CROSSVOLT TM	GlobalOptoisolator TM	POP TM	SuperSOT TM -3	
DenseTrench TM	GTO TM	Power247 TM	SuperSOT TM -6	
DOME TM	HiSeC TM	PowerTrench ^â	SuperSOT TM -8	
EcoSPARK TM	ISOPLANAR TM	QFET TM	SyncFET TM	
E ² CMOS TM	LittleFET TM	QS TM	TinyLogic TM	
EnSigna TM	MicroFET TM	QT Optoelectronics TM	TruTranslation TM	
FACT TM	MicroPak TM	Quiet Series TM	UHC TM	
FACT Quiet Series TM	MICROWIRE TM	SILENT SWITCHER ^â	UltraFET ^â	

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Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.